

UG4KB100-E-81C-T22

SINGLE PHASE GLASS PASSIVATED BRIDGE RECTIFIER

Voltage: 1000V

Current: 4.0A



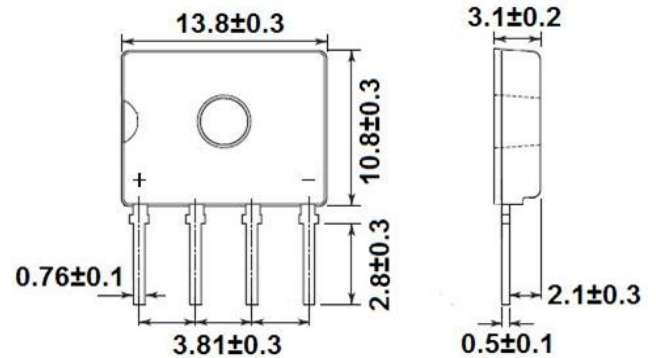
Features

Glass passivated chip junction
High case dielectric strength
High surge current capability
Ideal for printed circuit board
This series is UL listed under Recognized Component Index, file number E330278
Halogen Free

Mechanical Data

Terminal: Plated leads solderable per J-STD-002
Case: Halogen Free Epoxy
Polarity: Polarity symbol marked on body
Mounting position: any

D3K-T22



Dimensions in millimeters

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

(single-phase, half -wave, 60HZ, resistive or inductive load rating at 25°C, unless otherwise stated)

	Symbol	UG4KB100-E-81C-T22	units
Maximum repetitive peak reverse voltage	V _{rrm}	1000	V
Maximum RMS voltage	V _{rms}	700	V
Maximum DC blocking voltage	V _{dc}	1000	V
Maximum average forward rectified output current T _c 138°C with heatsink	I _{f(av)}	4.0	A
Peak forward surge current single sine-wave superimposed on rated load (JEDEC Method)	I _{fsm}	135	A
Maximum instantaneous forward voltage drop per leg at 2.0A	V _f	1.00	V
Rating for fusing (3ms ≤ t < 8.3ms)	I ² t	75	A ² Sec
Maximum DC reverse current at rated DC blocking voltage per leg	I _r	10.0 500	μA
Thermal resistance	R _{th(ja)} R _{th(jc)} R _{th(jl)}	55 1.5 15	°C/W
Operating junction and storage temperature range	T _j , T _{stg}	-55 to +150	°C

Note:

RATINGS AND CHARACTERISTIC CURVES UG4KB100-E-81C-T22

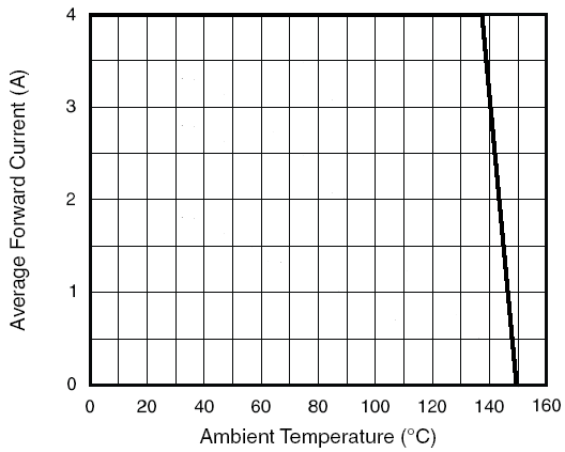


Figure 1. Forward Current Derating Curve

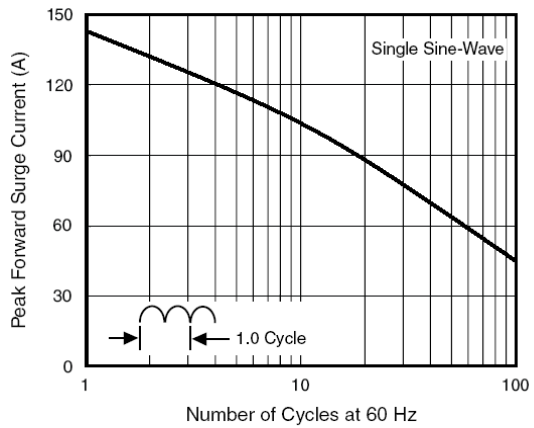


Figure 2. Maximum Non-Repetitive Peak Forward Surge Current Per Diode

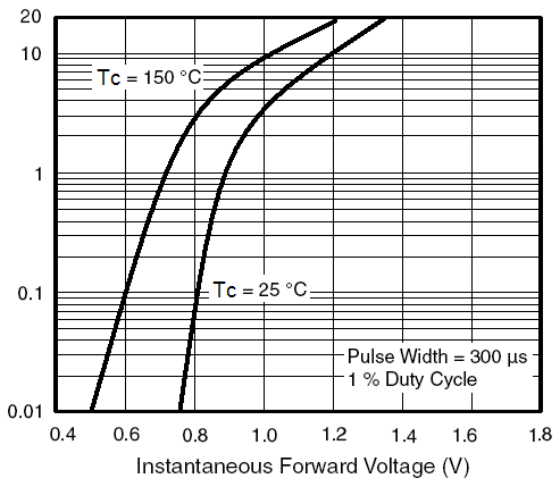


Figure 3. Typical Forward Characteristics Per Diode

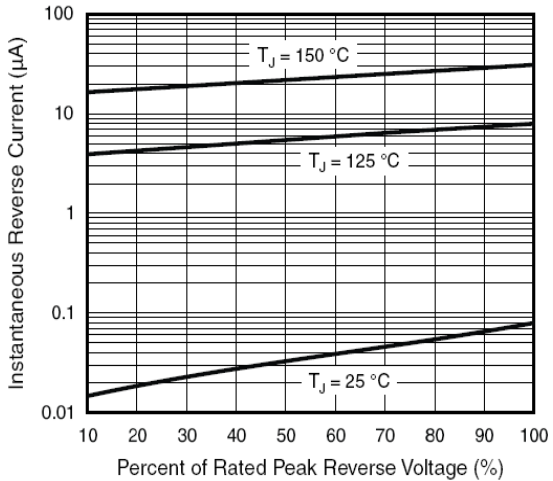


Figure 4. Typical Reverse Leakage Characteristics Per Diode

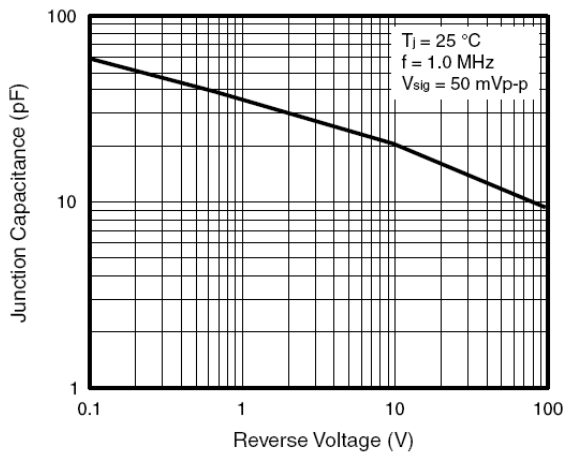


Figure 5. Typical Junction Capacitance Per Diode